## **Triacs**

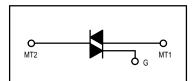
# **Silicon Bidirectional Triode Thyristors**

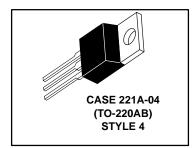
... designed primarily for full-wave ac control applications such as lighting sysjtems, heater controls, motor controls and power supplies; or wherever full-wave silicongate-controlled devices are needed.

- Off-State Voltages to 800 Volts
- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Thermal Resistance and High Heat Dissipation
- Gate Triggering Guaranteed in Three Modes (MAC223 Series) or Four Modes (MAC223A Series)

# MAC223 Series MAC223A Series

TRIACs 25 AMPERES RMS 200 thru 800 VOLTS





## **MAXIMUM RATINGS** ( $T_J = 25^{\circ}$ unless otherwise noted.)

Rating		Symbol	Value	Unit
Peak Repetitive Off-State Voltage (T <sub>J</sub> = -40 to 125°C) <sup>(1)</sup> (1/2 Sine Wave 50 to 60 Hz, Gate Open)	MAC223-4, MAC223A4 MAC223-6, MAC223A6 MAC223-8, MAC223A8 MAC223-10, MAC223A10	VDRM	200 400 600 800	Volts
On-State RMS Current (T <sub>C</sub> = 80°C) (Full Cycle Sine Wave 50 to 60 Hz)		I <sub>T(RMS)</sub>	25	Amps
Peak Non-repetitive Surge Current (One Full Cycle, 60 Hz, T <sub>C</sub> = 80°C, preceded and followed by rated current)		ITSM	250	Amps
Circuit Fusing (t = 8.3 ms)		l <sup>2</sup> t	260	A <sup>2</sup> s
Peak Gate Current (t ≤ 2 μs)		I <sub>GM</sub>	2	Amps
Peak Gate Voltage (t ≤ 2 μs)		V <sub>GM</sub>	±10	Volts
Peak Gate Power (t ≤ 2 μs)		P <sub>GM</sub>	20	Watts
Average Gate Power (T <sub>C</sub> = 80°C, t ≤ 8.3 ms)		P <sub>G</sub> (AV)	0.5	Watts
Operating Junction Temperature Range		TJ	-40 to 125	°C
Storage Temperature Range		T <sub>stg</sub>	-40 to 150	°C
Mounting Torque			8	in. lb.

<sup>1.</sup> V<sub>DRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



### **MAC223 Series MAC223A Series**

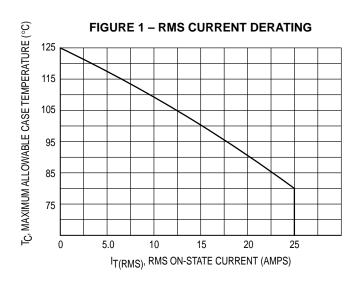
### THERMAL CHARACTERISTICS

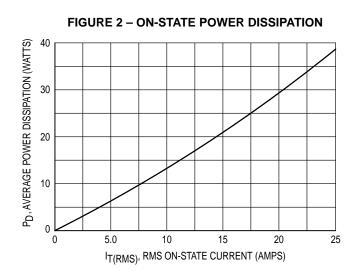
Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction to Case	$R_{ heta JC}$	1.2	°C/W	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	°C/W	

**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$  and either polarity of MT2 to MT1 voltage unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Blocking Current <sup>(1)</sup> $(V_D = Rated V_{DRM})  T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	<sup>I</sup> DRM	_	_	10 2	μA mA
Peak On-State Voltage (I <sub>TM</sub> = 35 A Peak, Pulse Width $\leq$ 2 ms, Duty Cycle $\leq$ 2%)	VTM		1.4	1.85	Volts
Gate Trigger Current (Continuous dc) $ (V_D=12\ V,\ R_L=100\ \Omega) \\ MT2(+),\ G(+);\ MT2(-),\ G(-);\ MT(+),\ G(-) \\ MT2(-),\ G(+)\ "A"\ SUFFIX\ ONLY $	<sup>I</sup> GT	_	20 30	50 75	mA
Gate Trigger Voltage (Continuous dc) $ (V_D=12\ V,\ R_L=100\ \Omega) $ $ MT2(+),\ G(+);\ MT2(-),\ G(-);\ MT(+),\ G(-) $ $ MT2(-),\ G(+)\ "A"\ SUFFIX\ ONLY $ $ (V_D=Rated\ V_{DRM},\ T_J=125^\circ C,\ R_L=10\ k) $ $ MT(+),\ G(+);\ MT2(-),\ G(-);\ MT2(+),\ G(-) $ $ MT2(-),\ G(+)\ "A"\ SUFFIX\ ONLY $	VGT	  0.2	1.1 1.3 0.4 0.4	2 2.5 —	Volts
Holding Current (V <sub>D</sub> = 12 V, I <sub>TM</sub> = 200 mA, Gate Open)	lн	_	10	50	mA
Gate Controlled Turn-On Time (V <sub>D</sub> = Rated V <sub>DRM</sub> , I <sub>TM</sub> = 35 A Peak, I <sub>G</sub> = 200 mA)	tgt	_	1.5	_	μs
Critical Rate of Rise of Off-State Voltage (VD = Rated VDRM, Exponential Waveform, TC = 125°C)	dv/dt	_	40	_	V/µs
Critical Rate of Rise of Commutation Voltage ( $V_D$ = Rated $V_{DRM}$ , $I_{TM}$ = 35 A Peak, Commutating di/dt = 12.6 A/ms, Gate Unenergized, $T_C$ = 80°C)	dv/dt(c)	_	5	_	V/µs

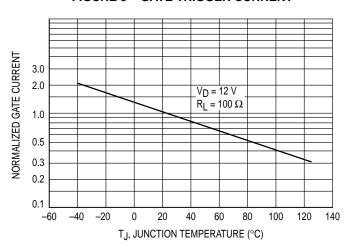
<sup>1.</sup> Ratings apply for open gate conditions. Devices shall not be tested with a constant current source for blocking voltage such that the voltage applied exceeds the rated blocking voltage.



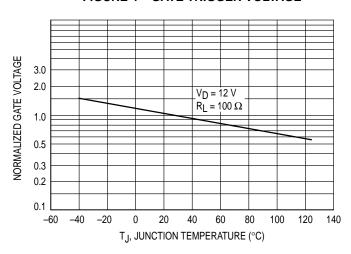


### **MAC223 Series MAC223A Series**

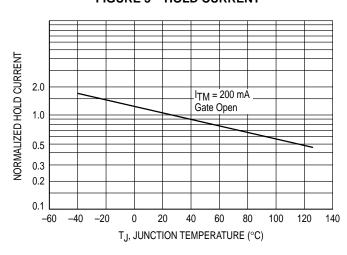
FIGURE 3 - GATE TRIGGER CURRENT



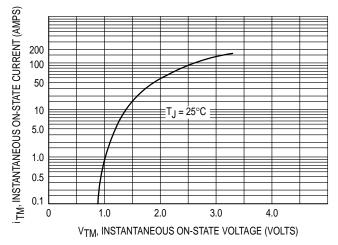
### FIGURE 4 - GATE TRIGGER VOLTAGE



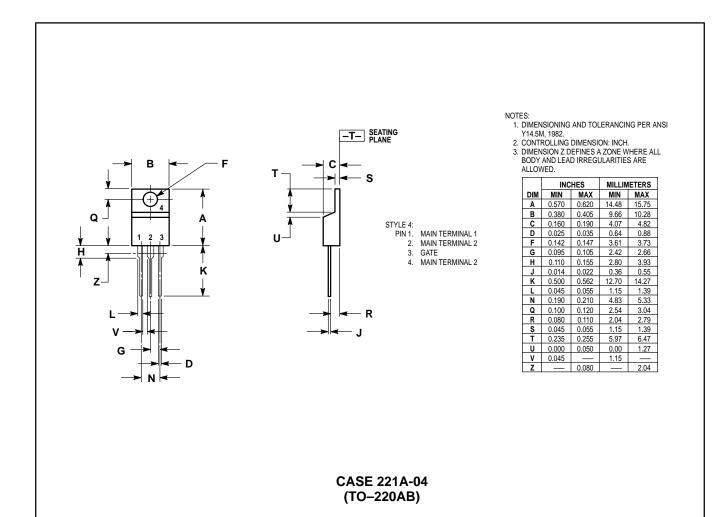
#### **FIGURE 5 – HOLD CURRENT**



### FIGURE 6 - TYPICAL ON-STATE CHARACTERISTICS



#### PACKAGE DIMENSIONS



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MAC223/D